

**Frenkel defect:**

- Ions(cations) missing from their lattice site occupy interstitial sites
- No effect on density
- There is a large difference in the size of the ions (cation or anions).

**Interstitial defect:**

- When some of the atoms occupy interstitial sites.
- It increases the density of a substance.

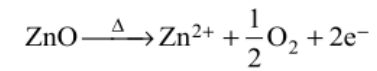
**Vacancy defect:**

- When some of the lattice sites are vacant.
- Decreases the density of the substances
- It develops on heating.

**Schottky defect:**

- Cations and anions are missing equally
- Density decreases
- It is shown by ionic substances in which ions (cations or anion) having almost similar sizes.

Due to presence of extra cations at interstitial sites e.g.,



$\text{Zn}^{2+}$  ions and the electrons occupy interstitial sites.

**Due to anionic vacancy (F-centres)**

When holes created by anions are occupied by electrons, these sites are called F-centres and are responsible for colour in the crystal. e.g., NaCl

**Metal deficiency defects:** It is due to missing of a cation from its lattice site and the presence of a cation having higher charge in the adjacent lattice site e.g., FeO

Metal excess defects

**Unit cell dimensions:**

$$d = \frac{Z \times M}{a^3 \times N_A}$$

Z = no. of atoms per unit cell  
d = density of solid  
a = edge length  
M = molar mass  
 $N_A$  = Avogadro's number

**Number of atoms per unit cell:**

Primitive cubic  $\Rightarrow 8 \times \frac{1}{8} = 1$

Body-centred cubic  
 $\Rightarrow 8 \times \frac{1}{8} + 1 = 2$

Face-centred cubic  
 $\Rightarrow 8 \times \frac{1}{8} + 6 \times \frac{1}{2} = 4$

**Body-centred:**

It contains one constituent particle at its body centre, besides the ones that are at its corners.

**Face centred:**

One constituent particles is present at the centre of each face.

**End-centred:** One constituent particles is present at the centre of any two opposite faces.

**Primitive unit cell:**

Constituent particles (atom, molecules or ions) are present on the corner positions only

**Centred unit cell:** Constituent particles are present on the corner position along with some other positions.

| Crystal system e.g.      | Axial distances or edge lengths | Axial angles                                      | Example                                                                                                 |
|--------------------------|---------------------------------|---------------------------------------------------|---------------------------------------------------------------------------------------------------------|
| Cubic                    | $a = b = c$                     | $\alpha = \beta = \gamma = 90^\circ$              | Zinc blend, KCl, NaCl, Cu                                                                               |
| Tetragonal               | $a = b \neq c$                  | $\alpha = \beta = \gamma = 90^\circ$              | Sn (white tin), $\text{TiO}_2$ , $\text{CaSO}_4$ , $\text{SnO}_2$                                       |
| Orthorhombic             | $a \neq b \neq c$               | $\alpha = \beta = \gamma = 90^\circ$              | Rhombic sulphur, $\text{KNO}_3$ , $\text{CaSO}_4$                                                       |
| Monoclinic               | $a \neq b \neq c$               | $\alpha = \gamma = 90^\circ; \beta \neq 90^\circ$ | Monoclinic sulphur, $\text{PbCrO}_4$ , $\text{Na}_2\text{SO}_4 \cdot 10\text{H}_2\text{O}$              |
| Hexagonal                | $a = b \neq c$                  | $\alpha = \gamma = 90^\circ; \beta = 120^\circ$   | Graphite, CdS, ZnO                                                                                      |
| Rhombohedral or Trigonal | $a = b = c$                     | $\alpha = \gamma = \beta \neq 90^\circ$           | $\text{CaCO}_3$ (calcite), HgS (cinnabar)                                                               |
| Triclinic                | $a \neq b \neq c$               | $\alpha \neq \gamma \neq \beta \neq 90^\circ$     | $\text{CuSO}_4 \cdot 5\text{H}_2\text{O}$ , $\text{H}_3\text{BO}_3$ , $\text{K}_2\text{Cr}_2\text{O}_7$ |

**Stoichiometric defects:** These defects do not disturb the stoichiometry of the solid

- They are also called intrinsic defects
- It increases with the increase in temperature (thermodynamic defects)

**Impurity defects:** Foreign atoms are present at the lattice site in place of host atoms or at vacant interstitial sites.

**Non-Stoichiometric defects:** The ratio of (+)ve and (-)ve ions present in the compound differs from that required by ideal formula.

**Line defects:** Deviation in entire rows of lattice point.

**Point defects:** Deviation around a point or an atom in a solid

**Unit cell:** Smallest repeating pattern

**Close packing in one dimension:** Lattice point arranged in a row C.N. = 2

**Close packing in two dimension:**

(a) Square close packaging: (A-A-A)...type C.N. = 4

(b) Hexagonal close packaging: (A-B-A-B type) C.N. = 6

**Close packing in three dimension:**

(a) Primitive cubic unit cell: AAA ... type arrangement, CN = 6, P.F. = 52.4%

(b) hcp = ABAB ... type pattern, C.N. = 12, PF = 74%

(c) ccp or fcc: ABCABC ... type pattern, CN = 12, PF = 74%

**Type of solids****Imperfection in solids****Properties of solids****Structure of solids****Close packed structure****Crystalline solids:**

- Definite characteristics
- Geometrical shape
- Long range order
- Anisotropic in nature e.g., NaCl,  $\text{KNO}_3$ , LiF, etc.

**Amorphous solids:**

- Irregular in shape
- Short range order
- Isotropic in nature e.g., plastic, glass, etc.

**SOLIDS**

**Doping:** The conductivity of an intrinsic semiconductor increases by adding an impurity which is electron rich or electron deficient as compared to Si or Ge. This process is called doping.

**Radius ratio rules:**

- The coordination number is a function of the sizes of the ions.
- Ionic radius ratios of cation and anion is very important in the determination of the crystal structures of an ionic substances.

Radius ratio = Radius of cation ( $r_+$ )/Radius of anion ( $r_-$ )

| Radius ratio | C.N. | shape              | Example                |
|--------------|------|--------------------|------------------------|
| 0.155-0.255  | 3    | Planar triangle    | $\text{B}_2\text{O}_3$ |
| 0.255-0.414  | 4    | Tetrahedral        | ZnS                    |
| 0.414-0.732  | 6    | Octahedral         | NaCl                   |
| 0.732-1.0    | 8    | Body-centred cubic | CsCl                   |

**Magnetic Properties:**

- Paramagnetic substances are weakly attracted by a magnetic field. e.g.,  $\text{O}_2$ ,  $\text{Cu}^{2+}$ ,  $\text{Cr}^{3+}$ .
  - Diamagnetic substances are weakly repelled by a magnetic field. e.g.  $\text{H}_2\text{O}$ ,  $\text{C}_6\text{H}_6$  and NaCl.
  - Ferromagnetic substances are those which show permanent magnetism even in the absence of magnetic field e.g., Fe, Ni, Co,  $\text{CrO}_2$  etc.
  - Anti-ferromagnetic substances are those which are expected to possess paramagnetism or ferromagnetism but actually have zero net magnetic moment due to equal number of domains in opposite directions, e.g., MnO.
  - Ferrimagnetic substances are those expected to have large magnetism but actually have small net magnetic moment
- $\uparrow \uparrow \uparrow \uparrow \uparrow \uparrow$  Ferromagnetic   
  $\uparrow \downarrow \uparrow \downarrow \uparrow \downarrow$  Antiferromagnetic   
  $\uparrow \uparrow \downarrow \uparrow \uparrow \downarrow$  Ferrimagnetic

**Electrical Properties**

- Conductors: Valence band is partially filled or it overlaps with a higher energy unoccupied conduction band
- Semiconductors: Small energy gap between valence and conduction band
- Insulators: Large energy gap between valence and conduction band

**p-type semiconductor** (by doping electron deficient impurities)

**n-type semiconductor** (by doping electron rich impurities)

| Type of solid | Intermolecular forces                   | Properties                                                                                                          |
|---------------|-----------------------------------------|---------------------------------------------------------------------------------------------------------------------|
| Ionic         | Ion-Ion forces                          | Brittle, hard, high melting point, insulator in solid but conductors in both fused and aqueous solutions e.g., NaCl |
| Molecular     | Dispersion forces/dipole dipole/H-bonds | Soft, low melting point, Insulators e.g. $\text{H}_2\text{O}$ , $\text{Br}_2$ , $\text{CO}_2$ , $\text{CH}_4$       |
| Covalent      | Covalent bonds                          | Hard, very high melting point e.g. C-diamond, $\text{SiO}_2$                                                        |
| Metallic      | Metallic bonds                          | Variable hardness and melting point, malleable and ductile, Conducting e.g. Na, Zn, Cu, Fe                          |